

List of Patents and Publications

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Patents Issued

51. US Pat. **8,253,109** "Slab scintillator with integrated two-sided photoreceiver," (with J. H. Abeles of Sarnoff Corp., filed Nov 2011, issued Aug 28, 2012)
50. US Pat. **8,158,941** "Bolometric sensor with high TCR and tunable low resistivity" (with Michael Gurvitch, Aleksandr Polyakov, Aleksandr Shabalov, filed 2010, issued 2012).
49. US Pat. **8,084,838** "Large-area PIN diode with reduced capacitance" (sole inventor, filed 2009, issued 2011)
48. US Pat. **7,876,795** "Semiconductor light source with electrically tunable emission wavelength" (with G. Belenky, J. Bruno, M. Kisin, L. Shterengas, S. Suchalkin, R. Tober, filed 2005, issued 2011)
47. US Pat. **7,643,718** "Photonic waveguide device for modal control," (with Arsen Subashiev; filed 2006, issued 2010)
46. US Pat. **7,326,637** "Method and system for bonding a semiconductor chip onto a carrier using micro-pins" (with S. Lee and M. Gurvitch; filed 2006, issued 2008).
45. US Pat. **7,310,361** "Intersubband semiconductor lasers with enhanced subband depopulation rate" (with G. Belenky *et al.*, filed 2004, issued 2007).
44. US Pat. **7,265,354** "Semiconductor scintillation high-energy radiation detector" (with Alexander Kastalsky and Boris Spivak; filed 2005, issued 2007).
43. US Pat. **7,064,432** "Method and system for bonding a semiconductor chip onto a carrier using micro-pins" (with S. Lee and M. Gurvitch; filed 2001, issued 2006).
42. US Pat. **6,944,407** "Method and apparatus for detecting radiation" [optical communication link] (with V. Gorfinkel and M. Gouzman; filed 2002, issued 2005).
41. US Pat. **6,934,030** "Method and apparatus for detecting radiation" [X-ray] (with Vera Gorfinkel and Mikhail Gouzman; filed 2002, issued 2005).
40. US Pat. **6,870,178** "Semiconductor laser with reduced temperature sensitivity" (with Levon Asryan, filed 2002, issued 2005).
39. US Pat. **6,819,696** "Intersubband semiconductor lasers with enhanced subband depopulation rate" (with G. Belenky *et al.*, filed 2001, issued 2004).
38. US Pat. **6,771,367** "Method and apparatus for detecting radiation," [electroluminescence] (with V. Gorfinkel and M. Gouzman; filed 2002, issued 2004).

37. US Pat. **6,760,109** “Method and apparatus for detecting radiation” [interacting EM radiation] (with Vera Gorfinkel and Mikhail Gouzman; filed 2002, issued 2004).
36. US Pat. **6,759,247** “Method and apparatus for detecting radiation,” [chemiluminescence] (with V. Gorfinkel and M. Gouzman; filed 2002, issued 2004).
35. US Pat. **6,528,801** “Method and apparatus for detecting radiation,” (with Vera Gorfinkel and Mikhail Gouzman; filed 1998, issued 2003).
34. US Pat. **6,497,804** “Method and apparatus for DNA sequencing” [network sequencer] (with Vera Gorfinkel and Mikhail Gouzman; filed 1999, issued 2002).
33. US Pat. **6,475,362** “Method and apparatus for compression of DNA samples for DNA sequencing” (with V. Gorfinkel and M. Gouzman; filed 1999, issued 2002).
32. US Pat. **6,464,852** “Multicapillary bundle for electrophoresis and detection for DNA” (with Vera Gorfinkel and Mikhail Gouzman; filed 1999, issued 2002).
31. US Pat. **6,370,560** “Load sharing controller for optimizing resource utilization cost” (with Tom Robertazzi and Saravut Charcranoon; filed 1998, issued 2002).
30. US Pat. **6,064,511** “Fabrication Methods and Structured Materials for Photonic Devices” (with C.Fortmann, J.Coleman, R.Tonucci; filed 1998, issued 2000).
29. US Pat. **6,038,023** “Sensors for Detection and Spectroscopy” (with Brad Carlson, Vera Gorfinkel and Mikhail Gouzman; filed 1998, issued 2000).
28. US Pat. **5,889,989** “Load Sharing Controller for Optimizing Monetary Cost” (with Tom Robertazzi and Jeeho Sohn; filed 1996, issued 1999).
27. US Pat. **5,784,157** “Method and apparatus for identifying fluorophores” (with V. B. Gorfinkel, filed 1995; issued 1998).
26. US Pat. **5,550,397** “Metal oxide semiconductor transistors having a polysilicon gate electrode with nonuniform doping in source-drain direction” (with N. Lifshitz, filed 1993, issued 1996).
25. US Pat. **5,496,743** “Method of making an article comprising a semiconductor device”, (filed 1993, issued 1996).
24. US Pat. **5,461,245** “Article comprising a bipolar transistor with a floating base” (with Z. S. Gribnikov, filed 1994, issued 1995).
23. US Pat. **5,457,709** “Unipolar semiconductor laser” [the first QCL patent] (with F. Capasso et al., filed 1994, issued 1995).

22. US Pat. **5,329,144** “A heterojunction bipolar transistor with a specific graded base structure” [enhanced diffusion of minority carriers] (filed 1993, issued 1994).
21. US Pat. **5,323,053** “Semiconductor devices using epitaxial silicides on (111) surfaces etched in (100) silicon substrates” (with G. L. Miller, filed 1992, issued 1994).
20. US Pat. **5,311,526** “Article that comprises a semiconductor laser, and method of operating the article” [dual modulation] (with V. Gorfinkel, filed 1993, issued 1994).
19. US Pat. **5,309,003** “Article comprising a real-space transfer semiconductor device and method of making the article” (filed 1992, issued 1994)
18. US Pat. **5,304,816** “Article comprising a ``ballistic" heterojunction bipolar transistor” (with A. A. Grinberg, filed 1992, issued 1994).
17. US Pat. **5,300,789** “Article comprising means for modulating the optical transparency of a semiconductor body, and method of operating the article” (with V. B. Gorfinkel, filed 1991, issued 1994).
16. US Pat. **5,223,723** “Light emitting device” (filed 1990, issued 1993).
15. US Pat. **5,206,526** “Staircase bandgap photodetector using recombination” (with C.-T. Liu, filed 1991, issued 1993).
14. US Pat. **5,146,078** “Articles and systems comprising optically communicating logic elements including an electro-optical logic element” (filed 1991, issued 1992).
13. US Pat. **5,012,486** “Vertical cavity semiconductor laser with lattice-mismatched mirror stack” (with Y.-H. Xie, filed 1990, issued 1991).
12. US Pat. **4,999,843** “Vertical semiconductor laser with lateral electrode contact to reduce resistive power loss” (with Y.-H. Xie, filed 1990, issued 1991).
11. US Pat. **4,999,687** “Logic element and article comprising the element", [*the RST device* **NORAND (ORNAND)**] (with M. R. Pinto, filed 1990, issued 1991).
10. US Pat. **4,903,092** “Real space electron transfer device using hot electron injection” (with A. Kastalsky, filed 1983, refiled 1986, refiled 1989; issued 1990).
9. US Pat. **4,860,064** “Transistor comprising a 2-dimensional carrier gas collector situated between emitter and gate” (sole inventor, filed 1987, issued 1989).
8. US Pat. **4,829,349** “Transistor having voltage-controlled thermionic emission” (with R. F. Kazarinov, filed 1983, issued 1989).

7. US Pat. **4,806,996** “Dislocation-free epitaxial layer on a lattice-mismatched porous or otherwise submicron patterned single crystal substrate” (sole inventor, filed 1986, refiled 1988; issued Feb 1989).
6. US Pat. **4,769,341** “Method of fabricating non-silicon materials on silicon substrate using an alloy of Sn and group IV semiconductors” (filed 1986, issued 1988).
5. US Pat. **4,725,870** “Silicon germanium photodetector” (with J. C. Bean and T. P. Pearsall, filed 1985, issued 1988).
4. US Pat. **4,704,622** “Negative transconductance device” (with F. Capasso, filed 1985, issued 1987).
3. US Pat. **4,691,215** “Hot electron unipolar transistor with two-dimensional degenerate electron gas base with continuously graded composition compound emitter” (filed 1985, issued 1987).
2. US Pat. **4,514,748** “Germanium p-i-n photodetector on silicon substrate” (with J. C. Bean and A. Kastalsky, filed 1983, issued 1985).
1. US Pat. **4,488,164** “Quantized Hall effect switching device” (with R. F. Kazarinov, filed 1982, issued 1984).

Patents Submitted/Pending

“Layered Semiconductor Scintillator,” RF File R-8324, with Arsen Subashiev; US Patent application, No. 13/316,706 (filed Dec 2011);

“Slab scintillator with integrated two-sided photoreceiver,” RF File R-8194, with J. H. Abeles of Sarnoff Corp.; US Patent application, No. 13/296,516 (filed Nov 2011);

“High-energy scintillation detector comprising multiple semiconductor slabs,” with A. Kastalsky; US Pat. Application Ser. No. 11/703,805 (filed 02/08/2007); Published Application Number 20080191138.

“Fiber-Optic Sensor for Measuring Level of Fluid,” RF File R-7574 (with M. Gouzman and O. Semenov; Ser. No 10/412948) Provisional application filed April, 2002; Full application April 14, 2003; Published Application Number: 20040021100.

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Journal Publications

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245. Serge Luryi, Oleg Semyonov, Arsen Subashiev, and Zhichao Chen, "Direct observation of Lévy flight of holes in bulk n-InP", submitted to Physical Review; arXiv:1205.4975v1 [<http://arxiv.org/abs/1205.4975>] (2012)
244. Serge Luryi and Arsen Subashiev, "Levy Flight of Holes in InP Semiconductor Scintillator", arXiv:1202.5576v1 [<http://arxiv.org/abs/1202.5576v1>] (to appear as invited paper in a book volume, WOFE-2011).
243. Oleg Semyonov, Arsen V. Subashiev, Zhichao Chen, and Serge Luryi, "Photon assisted Lévy flights of minority carriers in n-InP," *Journal of Luminescence* 132, pp. 1935-1943 (2012).
242. Oleg G. Semyonov, Arsen V. Subashiev, Alexander Shabalov, Nadia Lifshitz, Zhichao Chen, Takashi Hosoda, and Serge Luryi, "Reflectance reduction of InP wafers after high-temperature annealing", *Applied Optics* 51, pp. 5425–5431 (2012).

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241. Xiao Yun, Milutin Stanaćević and Serge Luryi, "Low-Power Amplifier for Readout Interface of Semiconductor Scintillator", *IEEE Transactions on Nuclear Science* vol. **58**, No. 4, pp. 2129-2136 (2011).
240. Serge Luryi and Arsen Subashiev, "Semiconductor scintillator based on photon recycling," *Nuclear Inst. and Methods in Physics Research A* **652**, pp. 292-294 (2011)..

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239. Arsen Subashiev, Oleg Semyonov, Zhichao Chen, and Serge Luryi, "Urbach tail studies by luminescence filtering in moderately doped bulk InP," *Applied Physics Letters* **97**, 181914 (2010)
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237. Oleg Semyonov, Arsen Subashiev, Zhichao Chen, and Serge Luryi, "Radiation efficiency of heavily doped bulk n-InP semiconductor," *Journal of Applied Physics* **108**, 013101, pp. 1-7 (2010)

236. Serge Luryi and Arsen Subashiev, "Semiconductor Scintillator for 3-Dimensional Array of Radiation Detectors", in *Future Trends in Microelectronics: From Nanophotonics to Sensors to Energy*, ed. by S. Luryi, J. M. Xu, and A. Zaslavsky, Wiley Interscience, Hoboken, New Jersey (2010) pp. 331-346.
235. Arsen Subashiev and Serge Luryi, "Semiconductor gamma radiation detectors: band structure effects in energy resolution", in *Future Trends in Microelectronics: From Nanophotonics to Sensors to Energy*, ed. by S. Luryi, J. M. Xu, and A. Zaslavsky, Wiley Interscience, Hoboken, New Jersey (2010) pp.347-363.
234. M. Gurvitch, S. Luryi, A. Polyakov, A. Shabalov, "Treating the case of incurable hysteresis in VO₂", in *Future Trends in Microelectronics: From Nanophotonics to Sensors to Energy*, ed. by S. Luryi, J. M. Xu, and A. Zaslavsky, Wiley Interscience, Hoboken, New Jersey (2010) pp. 395-409.
233. M. Gurvitch, S. Luryi, A. Polyakov, A. Shabalov, "Nonhysteretic phenomena in the Metal-Semiconductor Phase-Transition Loop of VO₂ Films for Bolometric Sensor Applications", *IEEE Transactions on Nanotechnology* (2010) in print.

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232. Arsen Subashiev and Serge Luryi, "Correlation effects in sequential energy branching: an exactly solvable model of the Fano statistics", *Physical Review E* **81**, 021123 [pp. 1-10] (2010); see also arXiv:0911.1532 .
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228. M. Gurvitch, S. Luryi, A. Polyakov, A. Shabalov, "Non-hysteretic branches inside the hysteresis loop in VO₂ films for focal plane array imaging bolometers", arXiv:0805.3566 (May 23, 2008).
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214. A. Kastalsky, S. Luryi, and B. Spivak, "Semiconductor high-energy radiation scintillation detector", *Nucl. Instr. Meth. in Phys. Research A* **565**, pp. 650-656 (2006).

213. Serge Luryi, "Physics, Philosophy, and ... Ecology", *Physics Today*, Vol. **59**, No 5, p. 51 (May 2006).

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